

Is Now Part of



ON Semiconductor®

To learn more about ON Semiconductor, please visit our website at www.onsemi.com

Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (_), the underscore (_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.onsemi.com. Please email any questions regarding the system integration to Fairchild guestions@onsemi.com.

ON Semiconductor and the ON Semiconductor logo are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any EDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officer



FDBL0110N60

January 2016

N-Channel PowerTrench[®] MOSFET 60 V, 300 A, 1.1 m Ω

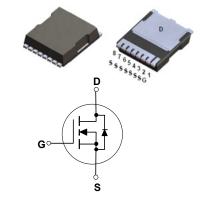
Features

- Typical $R_{DS(on)}$ = 0.85 m Ω at V_{GS} = 10V, I_D = 80 A
- Typical $Q_{g(tot)}$ = 170 nC at V_{GS} = 10V, I_D = 80 A
- UIS Capability
- RoHS Compliant

Applications

- Industrial Motor Drive
- Industrial Power Supply
- Industrial Automation
- Battery Operated tools
- Battery Protection
- Solar Inverters
- UPS and Energy Inverters
- Energy Storage
- Load Switch





For current package drawing, please refer to the Fairchild website at https://www.fairchildsemi.com/evaluate/package-specifications/packageDetails.ht-ml?id=PN_PSOFA-008

MOSFET Maximum Ratings $T_J = 25$ °C unless otherwise noted.

Symbol	Parameter	Ratings	Units	
V_{DSS}	Drain-to-Source Voltage		60	V
V_{GS}	Gate-to-Source Voltage		±20	V
	Drain Current - Continuous (V _{GS} =10) (Note 1)	T _C = 25°C	300	Α
'D	Pulsed Drain Current	T _C = 25°C	See Figure 4	^
E _{AS}	Single Pulse Avalanche Energy	(Note 2)	1167	mJ
D	Power Dissipation		429	W
P_{D}	Derate Above 25°C		2.86	W/°C
T _J , T _{STG}	Operating and Storage Temperature		-55 to + 175	°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case		0.35	°C/W
$R_{\theta JA}$	Maximum Thermal Resistance, Junction to Ambient	(Note 3)	43	°C/W

Notes:

- 1: Current is limited by bondwire configuration.
- 2: Starting $T_J = 25$ °C, L = 0.57mH, $I_{AS} = 64$ A, $V_{DD} = 40$ V during inductor charging and $V_{DD} = 0$ V during time in avalanche.
- 3: R_{0,JA} is the sum of the junction-to-case and case-to-ambient thermal resistance, where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{0,JC} is guaranteed by design, while R_{0,JA} is determined by the board design. The maximum rating presented here is based on mounting on a 1 in² pad of 2oz copper.

Package Marking and Ordering Information

Device Marking	Device	Package			
FDBL0110N60	FDBL0110N60	MO-299A	-	-	-

©2014 Fairchild Semiconductor Corporation FDBL0110N60 Rev.1.2

www.fairchildsemi.com

Units

Max.

Electrical Characteristics $T_J = 25^{\circ}C$ unless otherwise noted.

Parameter

Off Characteristics								
B _{VDSS}	Drain-to-Source Breakdown Voltage	$I_D = 250 \mu A$,	V _{GS} = 0V	60	-	-	٧	
I _{DSS}	Drain-to-Source Leakage Current	V _{DS} = 60V	$T_{\rm J} = 25^{\rm o}{\rm C}$	-	-	1	μА	
		$V_{GS} = 0V$	$T_J = 175^{\circ}C \text{ (Note 4)}$	-	-	1	mA	
I _{GSS}	Gate-to-Source Leakage Current	$V_{GS} = \pm 20V$		-	-	±100	nA	

Test Conditions

Min.

Тур.

On Characteristics

Symbol

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250 \mu A$		2.0	3.0	4.0	V
R _{DS(on)}	Drain to Source On Resistance	I _D = 80A,	$T_{J} = 25^{\circ}C$	-	0.85	1.1	mΩ
		V _{GS} = 10V	$T_J = 175^{\circ}C \text{ (Note 4)}$	-	1.5	2.2	mΩ

Dynamic Characteristics

C _{iss}	Input Capacitance), 00\/ \/ 0\/		-	13650	-	pF
C _{oss}	Output Capacitance		$-V_{DS} = 30V, V_{GS} = 0V,$ - f = 1MHz		3375	-	pF
C _{rss}	Reverse Transfer Capacitance	I - IIVII IZ			255	-	pF
R_g	Gate Resistance	f = 1MHz	f = 1MHz		2.3	-	Ω
$Q_{g(ToT)}$	Total Gate Charge at 10V	$V_{GS} = 0$ to 10V	V _{DD} = 48V	-	170	220	nC
$Q_{g(th)}$	Threshold Gate Charge	$V_{GS} = 0 \text{ to } 2V$	$V_{GS} = 0 \text{ to } 2V$ $I_D = 80A$		24	32	nC
Q_{gs}	Gate-to-Source Gate Charge		_	-	56	-	nC
Q_{gd}	Gate-to-Drain "Miller" Charge			-	24	-	nC

Switching Characteristics

t _{on}	Turn-On Time	V_{DD} = 30V, I_{D} = 80A, V_{GS} = 10V, R_{GEN} = 6 Ω	-	-	137	ns
t _{d(on)}	Turn-On Delay		-	45	1	ns
t _r	Rise Time		-	61	-	ns
t _{d(off)}	Turn-Off Delay		-	80	-	ns
t _f	Fall Time		-	41	-	ns
t _{off}	Turn-Off Time		-	-	156	ns

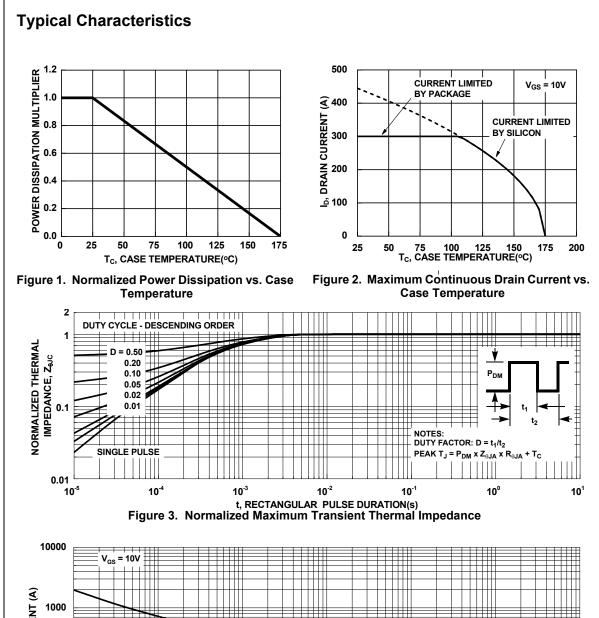
Drain-Source Diode Characteristics

I _S	Maximum Continuous Drain to Source	Maximum Continuous Drain to Source Diode Forward Current			300	Α
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current			-	See Figure 4	Α
\/	Source-to-Drain Diode Voltage	I _{SD} =80A, V _{GS} = 0V	-	-	1.25	V
V_{SD}		$I_{SD} = 40A, V_{GS} = 0V$	-	-	1.2	V
t _{rr}	Reverse-Recovery Time	$I_F = 80A$, $dI_{SD}/dt = 100A/\mu s$,	-	107	139	ns
Q _{rr}	Reverse-Recovery Charge	V _{DD} =48V	-	183	265	nC

Note:

4: The maximum value is specified by design at T_J = 175°C. Product is not tested to this condition in production.

FDBL0110N60 Rev.1.2 2 www.fairchildsemi.com



IDM, PEAK CURRENT (A) T_C = 25°C FOR TEMPERATURES 100 ABOVE 25°C DERATE PEAK **CURRENT AS FOLLOWS:** 175 - T_C SINGLE PULSE 10 10⁻⁵ 10⁻² 10⁻⁴ 10⁻³ 10⁻¹ 10° 10¹ t, RECTANGULAR PULSE DURATION(s)

Figure 4. Peak Current Capability

Typical Characteristics

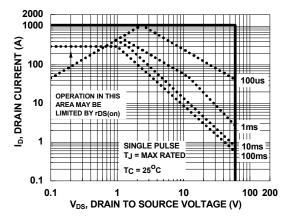
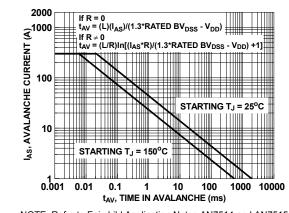


Figure 5. Forward Bias Safe Operating Area



NOTE: Refer to Fairchild Application Notes AN7514 and AN7515

Figure 6. Unclamped Inductive Switching

Capability

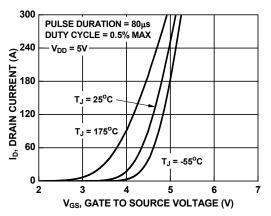


Figure 7. Transfer Characteristics

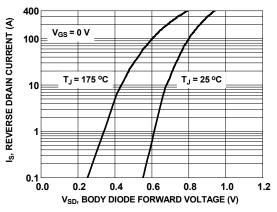


Figure 8. Forward Diode Characteristics

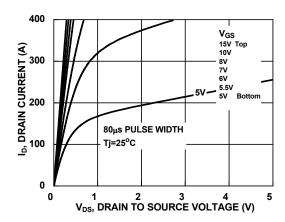


Figure 9. Saturation Characteristics

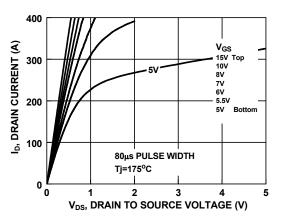
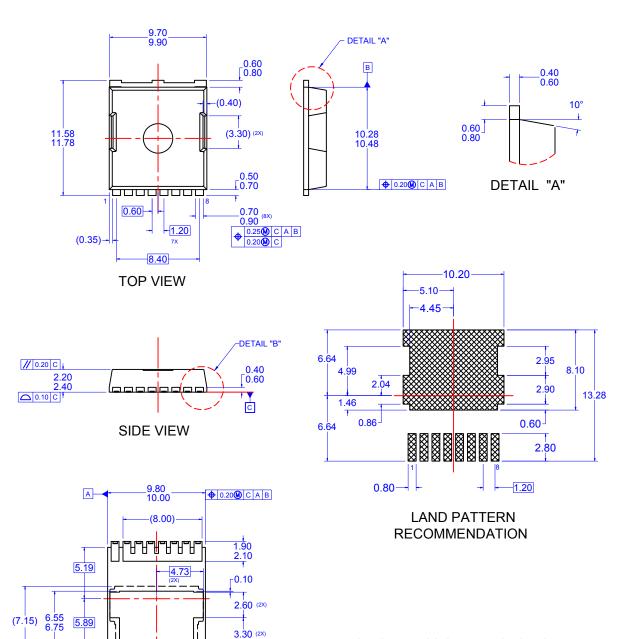


Figure 10. Saturation Characteristics

FDBL0110N60 Rev.1.2 4 www.fairchildsemi.com



NOTES: UNLESS OTHERWISE SPECIFIED

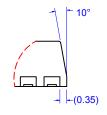
- A) PACKAGE STANDARD REFERENCE: JEDEC MO-299, ISSUE A, DATED NOVEMBER 2009.
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSIONS DO NOT INCLUDE BURRS OR MOLD FLASH. MOLD FLASH OR BURRS DOES NOT EXCEED 0.10MM.
- D) DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.
- E) DRAWING FILE NAME: MKT-PSOF08AREV3

BOTTOM VIEW

7.60

- - 1.20

3.75



0.65-

DETAIL "B"

ON Semiconductor and in are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hol

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800–282–9855 Toll Free USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910

Phone: 421 33 790 2910

Japan Customer Focus Center
Phone: 81–3–5817–1050

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

© Semiconductor Components Industries, LLC

www.onsemi.com